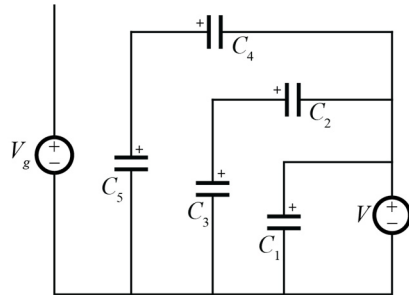
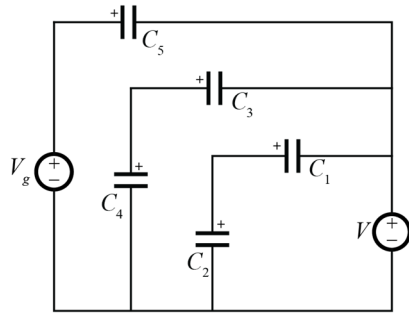
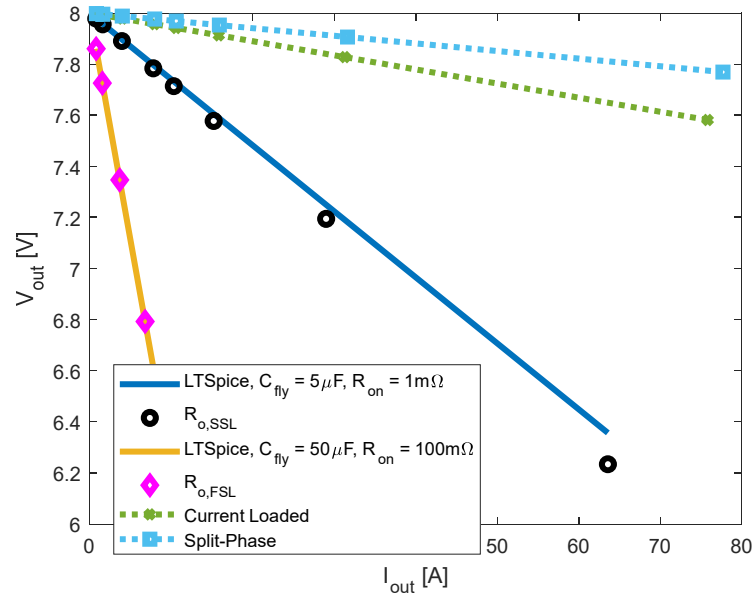


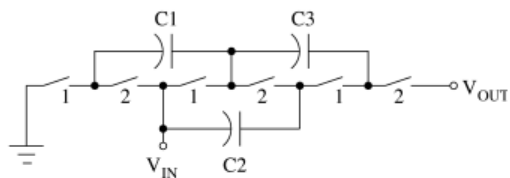
# Split-Phase Control



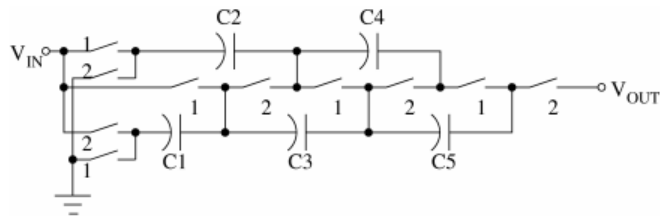
# LTSpice Simulation



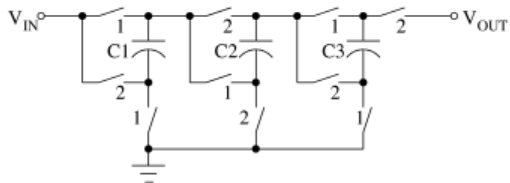
# Complete Soft Charging



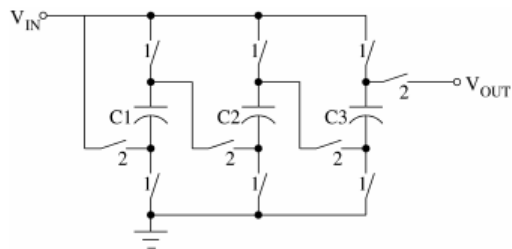
a) Ladder



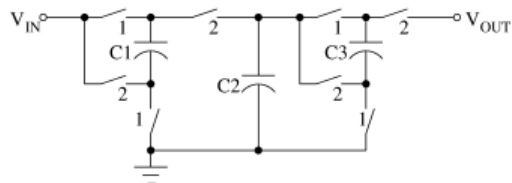
b) Dickson Charge Pump



c) Fibonacci

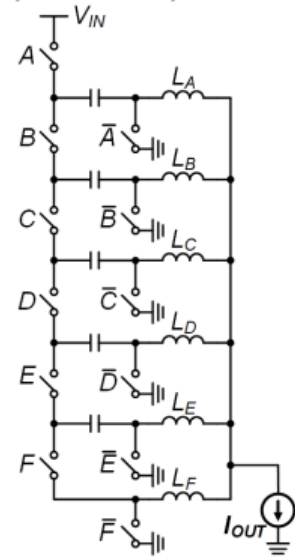
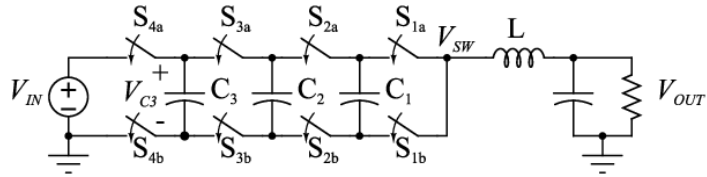


d) Series-Parallel

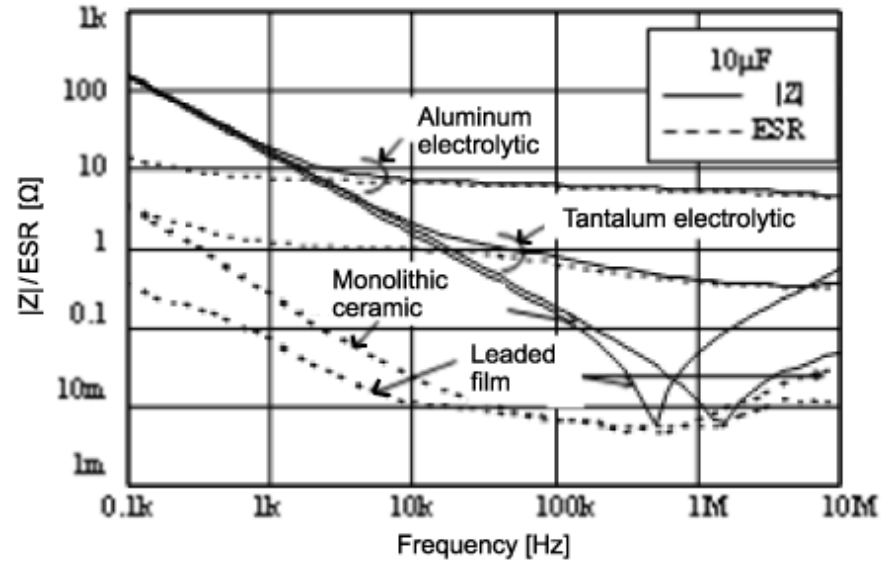


e) Doubler

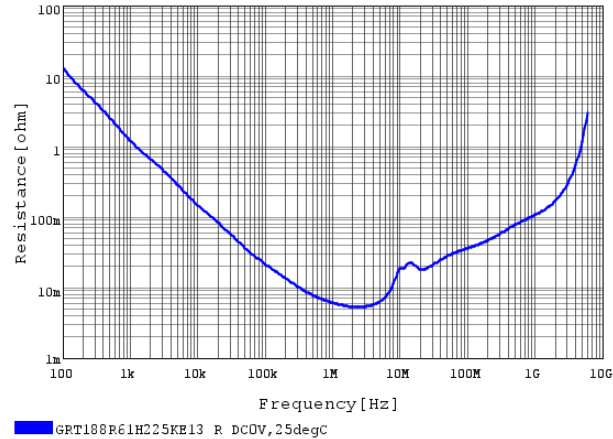
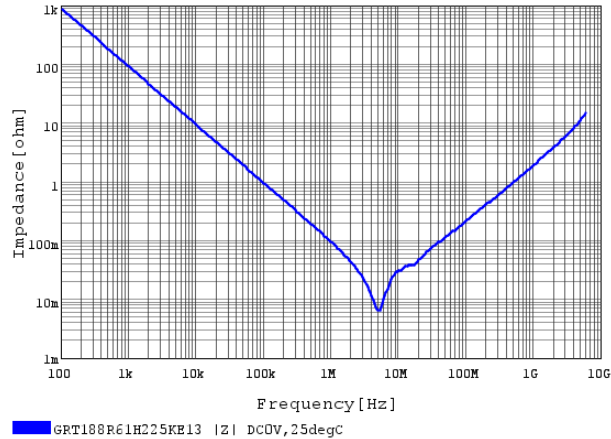
# FCML and SC Buck



# Types of Capacitors



# Ceramic Capacitor Impedance and Resistance



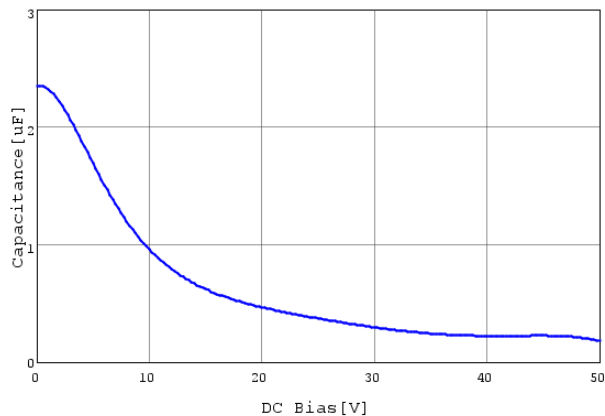
## Capacitor data sources

- Murata Simsurfing
- TDK SEAT

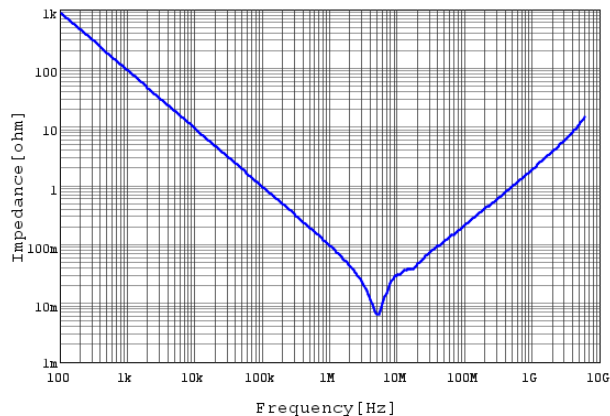
# MLCC

- Capacitor codes, e.g. X7R or C0G standardized to define stability over temperature
  - **Class-II:** Codes begin with X, Y, or Z (e.g. X7R, Y5V)
  - **Class-I:** Codes begin with [CBLAMPRTVU] (e.g. C0G, NPO)

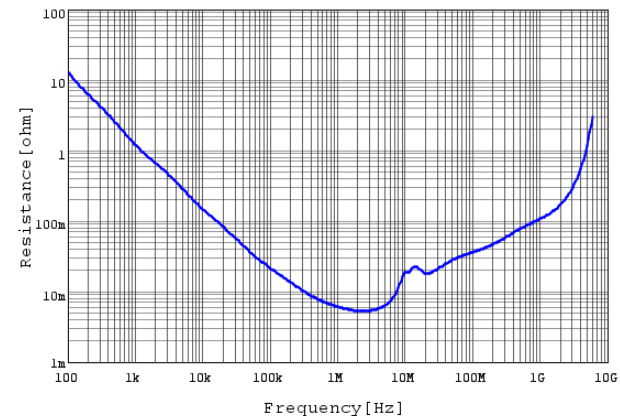
# 2.2 $\mu$ F, 50V X7R (Class-II) 0603 footprint



GRT188R61H225KE13 C-DC bias capacitance, 25.0degC, AC1Vrms



GRT188R61H225KE13 |Z| DC0V,25degC

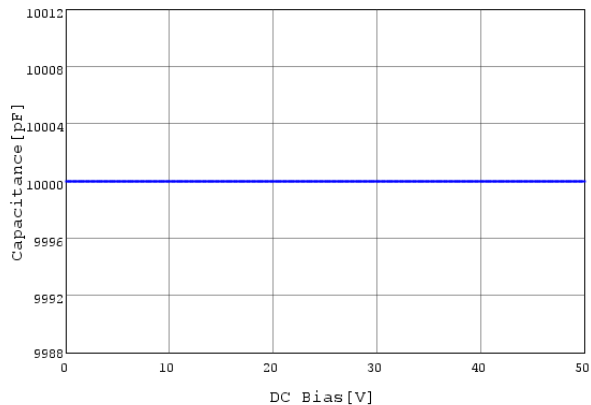


GRT188R61H225KE13 R DC0V,25degC

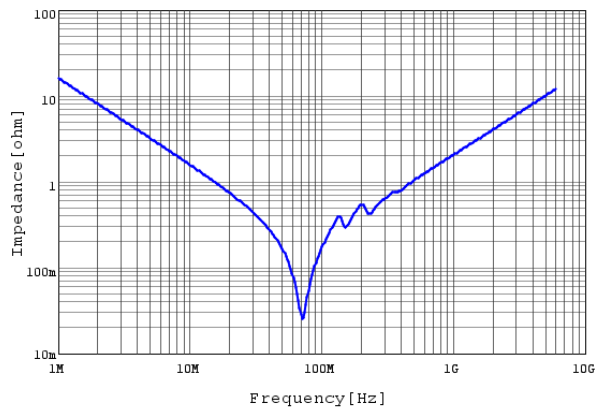
Remaining: 7.2% at full voltage



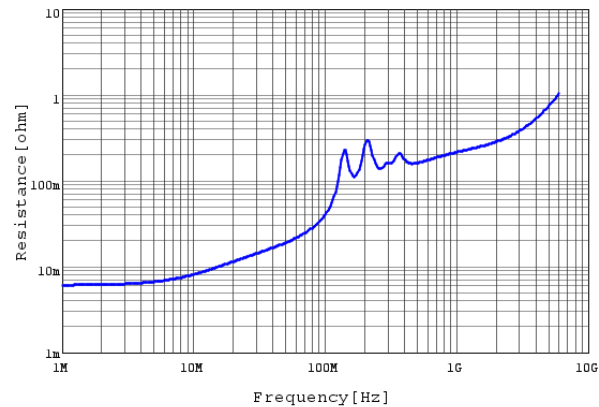
# 10nF, 50V COG (Class-I) 0603 footprint



GRT1885C1H103JA02 C-DC bias capacitance, 25.0degC, AC1Vrms

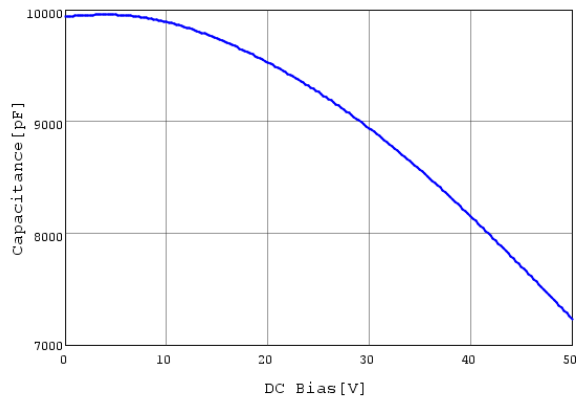


GRT1885C1H103JA02 |Z| DC0V,25degC

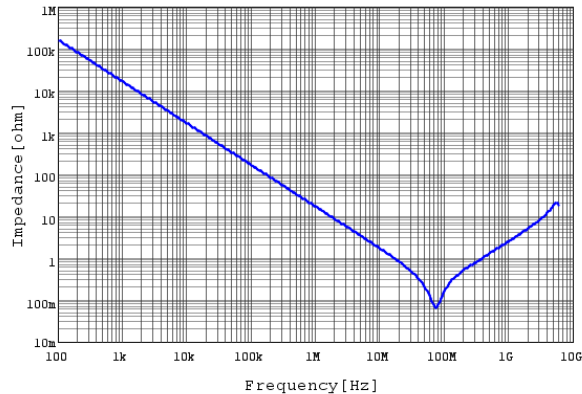


GRT1885C1H103JA02 R DC0V,25degC

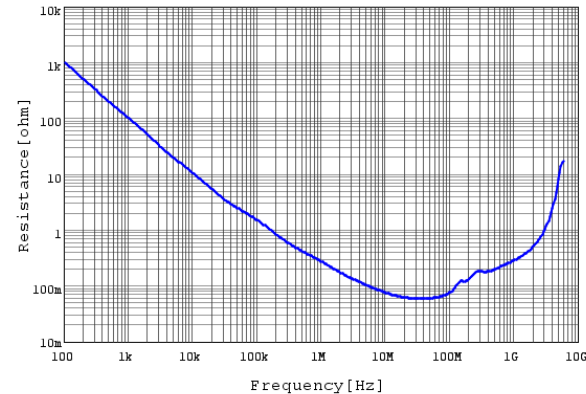
# 10nF, 50V X7R (Class-II) 0603 footprint



■ GRM188R71H103MA01 C-DC bias capacitance, 25.0degC, AC1.0Vrms

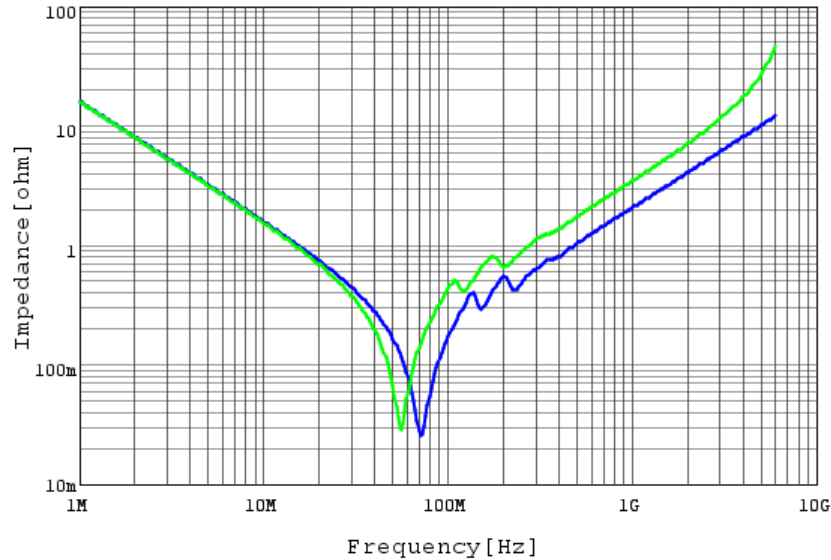


■ GRM188R71H103MA01 |Z| DC0V,25degC



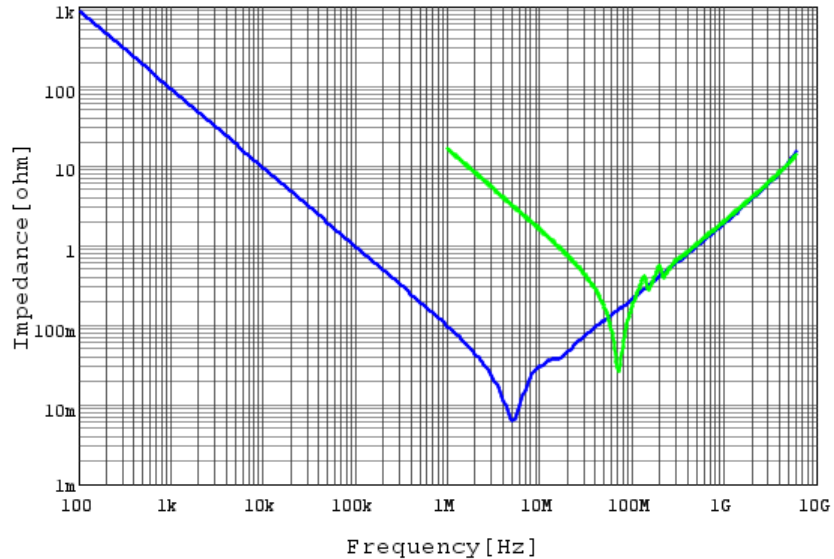
■ GRM188R71H103MA01 R DC0V,25degC

# 10nF, 50V COG (Class-I) varied footprint



■ GPM1885C1H103JA01 |Z| DCOV, 25degC **0603**  
■ GPM3195C1H103JA01 |Z| DCOV, 25degC **1206**

# Same 0603 Footprint



**■** GRT188R61H225KE13 |Z| DCOV,25degC **2.2µF X5R**

**■** GCM1885C1H103GA16 |Z| DCOV,25degC **10nF COG**

# Class-II Capacitor Hysteresis Loss

TABLE II  
EMPLOYED COMPONENTS

Component	Dielectric	Manufacturer	Part Number	$V_n$	$C_n$	N(parallel)	$C_{tot}$	DF
$C_{cal}$	C0G	TDK	CAA572C0G2J204J640LH	650 V	200 nF	2	400 nF	< 0.02 %
$C_{ref}$	C0G	TDK	C5750C0G2A154J230KE	100 V	150 nF	32	4.8 $\mu$ F	< 0.03 %
$C_{DUT}$	X7R	Knowles Syfer	2220Y1K00474KETWS2	1 kV	470 nF	1	470 nF	> 0.71 %

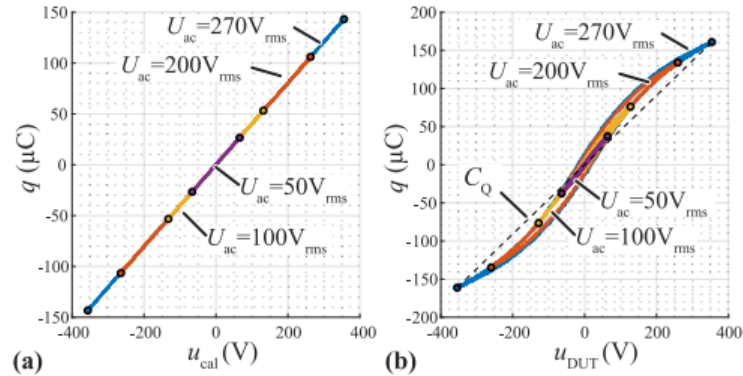


Fig. 6.  $U - Q$  hysteresis recorded at 50 Hz for a range of excitation voltages for (a) the calibration capacitor, which shows no hysteresis and has a constant  $C_Q = C_d$  at all voltages, and (b) the DUT, which exhibits increasing hysteresis and losses with increasing excitation voltage.  $C_Q$  highlighted for  $U_{ac} = 270 \text{ V}_{rms}$ . Measured  $U - Q$  curves are identical at 50 Hz and 100 Hz.

# $C_{OSS}$ Hysteresis

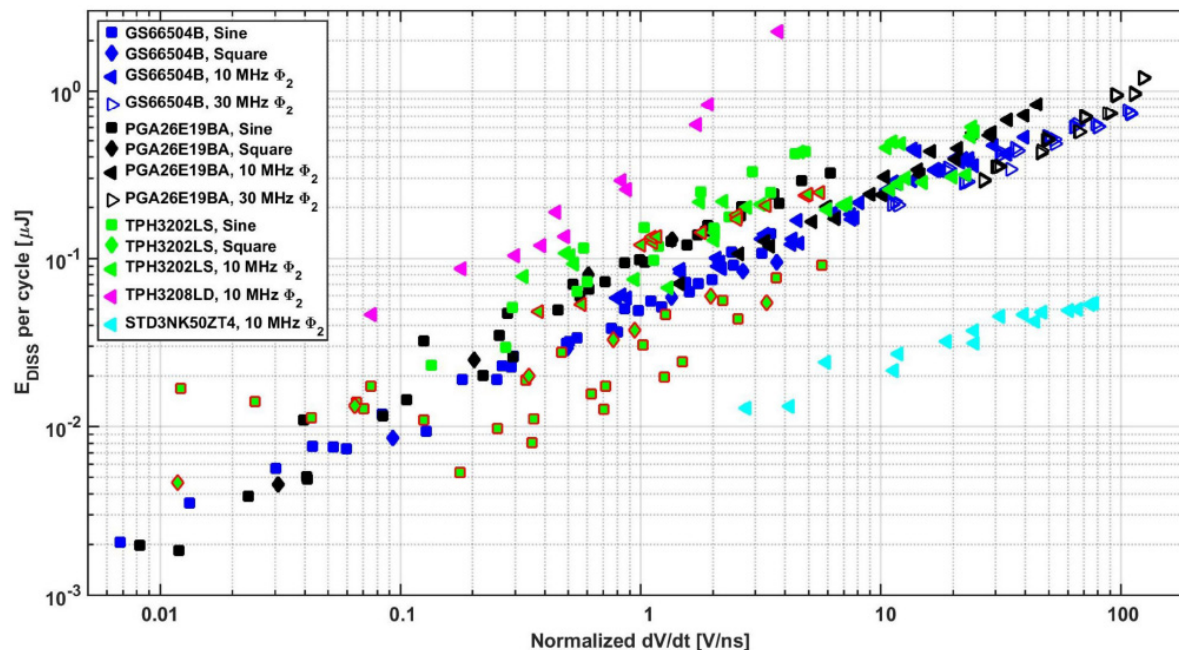


Fig. 15. Losses per cycle versus normalized, by (8),  $dV/dt$  for the three studied devices and two additional “extreme performance” devices. The red outline around the TPH3202LS results indicates applied voltages under 300 V and  $\beta = 1.46$  in (8). All recorded measurements are included here. There are no measurements for the TPH3202LS 30 MHz  $\Phi_2$ , as the  $\Phi_2$  wave generator could not be tuned to maintain ZVS with the TPH3202LS device and  $C_{REF}$  in parallel.

# Transistor Structure and Material

SiC

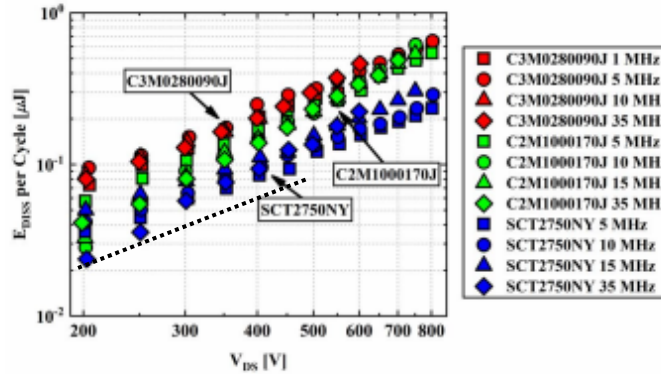
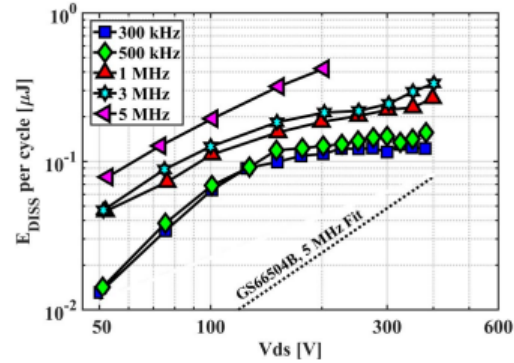


Fig. 4:  $C_{OSS}$  losses for three devices from 1-35 MHz.

Si Superjunction



(b) High-frequency  $C_{OSS}$  losses for the R6011KNTJL device.

Fig. 6: Silicon superjunction  $C_{OSS}$  loss data.

Si

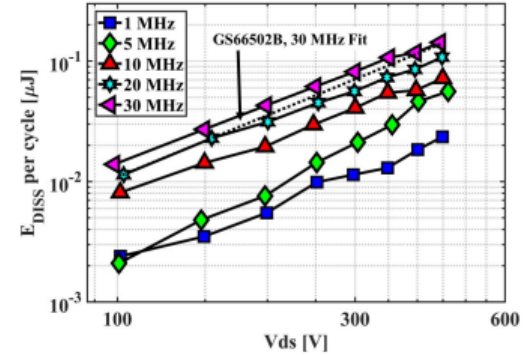


Fig. 7:  $C_{OSS}$  losses for STD3NK50ZT4.

